



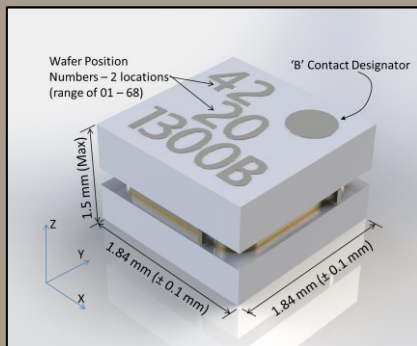
Micro G Switch Bottom Contact Model AT-1300-B

FEATURES:

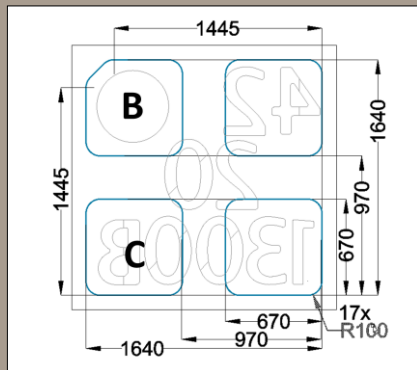
- Small and Lightweight – 3.4 mm²
- Extremely Fast Response Times
- High Shock Survivability – 65,000+ g
- Surface Mount – Au over Ni Pads
- Tape and Reel Packaging
- Environmental Seal

APPLICATIONS:

- Impact Detection
- Arming / Fuzing
- Artillery, Launch
- More



AT-1300-B Device Dimensions



AT-1300-B Pad Dimensions (micrometers) as viewed from pad side of device

Specifications

OPERATING CHARACTERISTICS:

Sensitivity	+Z (normal to PCB)	
Contact Acceleration Threshold	1000 to 1600	g
Contact Type (3)	Normally Open, Non-Latching	
Response Time (2)	< 50	µs
Reset	Automatic with g decay	

ELECTRICAL CHARACTERISTICS

Contact Resistance (1)	< 10	ohms
Insulation Resistance (min.)	1000	Mohm
Breakdown Voltage.....	>200	VDC

ENVIRONMENTAL RATINGS:

Operate Temperature Range.....	-55 to +125	°C
Storage Temperature Range.....	-55 to +125	°C
PCB/Pad Shear Force	> 20	N
Shock Survival (4)	>65000	g

PHYSICAL CHARACTERISTICS:

Nominal Dimensions (LxWxH).....	1.84 x 1.84 x 1.3	mm
Volume.....	3.7	mm ³
Mass	20	milligrams
ROHS Compliant ?	Yes	

- (1) Contact resistance is dependent on input pulse acceleration level.
- (2) Response time depends upon input pulse profile
- (3) Electrical connection between pads B (bottom) and C (common) is normally open and is closed while acceleration is greater than the contact acceleration threshold.
- (4) The Micro G Switch devices are designed to survive the extreme high shock environments associated with artillery launch events.

Note that the information on this data sheet is for reference only.

As each application may have unique requirements, please verify the specifications as well as suitability of using our products in your applications by consulting our engineering department.

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